SEMICONDUCTOR TM

## MM74HC132 Quad 2-Input NAND Schmitt Trigger

#### **General Description**

The MM74HC132 utilizes advanced silicon-gate CMOS technology to achieve the low power dissipation and high noise immunity of standard CMOS, as well as the capability to drive 10 LS-TTL loads.

The 74HC logic family is functionally and pinout compatible with the standard 74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to  $V_{CC}$  and ground.

#### Features

- Typical propagation delay: 12 ns
- Wide power supply range: 2V–6V
- Low quiescent current: 20 µA maximum (74HC Series)

September 1983

Revised January 2005

- Low input current: 1 μA maximum
- Fanout of 10 LS-TTL loads

Logic Diagram

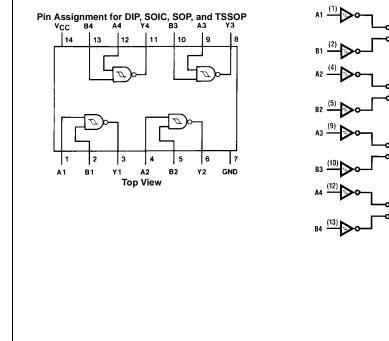
Typical hysteresis voltage: 0.9V at V<sub>CC</sub>=4.5V

### **Ordering Code:**

Order Number	Package Number	Package Description
MM74HC132M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
MM74HC132MX_NL	M14A	Pb-Free 14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
MM74HC132SJ	M14D	Pb-Free 14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
MM74HC132MTC	MTC14	14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide
MM74HC132N	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide

Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code. (Tape and Reel not available in N14A.) Pb-Free package per JEDEC J-STD-020B.

## **Connection Diagram**



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Y = AB

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(Note 2)

## Absolute Maximum Ratings(Note 1)

# Recommended Operating Conditions

Supply Voltage (V <sub>CC</sub> )	-0.5 to +7.0V
DC Input Voltage (V <sub>IN</sub> )	–1.5 to $V_{CC}$ +1.5V
DC Output Voltage (V <sub>OUT</sub> )	–0.5 to V <sub>CC</sub> +0.5V
Clamp Diode Current (I <sub>IK</sub> , I <sub>OK</sub> )	±20 mA
DC Output Current, per pin (I <sub>OUT</sub> )	±25 mA
DC V <sub>CC</sub> or GND Current, per pin (I <sub>CC</sub> )	±50 mA
Storage Temperature Range (T <sub>STG</sub> )	$-65^{\circ}C$ to $+150^{\circ}C$
Power Dissipation (P <sub>D</sub> )	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature (T <sub>L</sub> )	
(Soldering 10 seconds)	260°C

	Min	Max	Units
Supply Voltage (V <sub>CC</sub> )	2	6	V
DC Input or Output Voltage	0	V <sub>CC</sub>	V
(V <sub>IN</sub> , V <sub>OUT</sub> )			
Operating Temperature Range (T <sub>A</sub> )	-40	+125	°C

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur. Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Prover Dissipation temperature derating — plastic "N" package: – 12 mW/°C from 65°C to 85°C.

## DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	v <sub>cc</sub>	T <sub>A</sub> = 25°C		T <sub>A</sub> = -40 to 85°C	T <sub>A</sub> = -40 to 125°C	Units	
Symbol	Faianietei	conditions		Тур	Guaranteed Limits		imits	Units	
$V_{T+}$	Positive Going	Min	2.0V		1.0	1.0	1.0	V	
	Threshold Voltage		4.5V		2.0	2.0	2.0	V	
			6.0V		3.0	3.0	3.0	V	
		Max	2.0V		1.5	1.5	1.5	V	
			4.5V		3.15	3.15	3.15	V	
			6.0V		4.2	4.2	4.2	V	
V <sub>T-</sub>	Negative Going	Min	2.0V		0.3	0.3	0.3	V	
	Threshold Voltage		4.5V		0.9	0.9	0.9	V	
			6.0V		1.2	1.2	1.2	V	
		Max	2.0V		1.0	1.0	1.0	V	
			4.5V		2.2	2.2	2.2	V	
			6.0V		3.0	3.0	3.0	V	
V <sub>H</sub>	Hysteresis Voltage	Min	2.0V		0.2	0.2	0.2	V	
			4.5V		0.4	0.4	0.4	V	
			6.0V		0.5	0.5	0.5	V	
		Max	2.0V		1.0	1.0	1.0	V	
			4.5V		1.4	1.4	1.4	V	
			6.0V		1.5	1.5	1.5	V	
V <sub>OH</sub>	Minimum HIGH Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$	2.0V	2.0	1.9	1.9	1.9	V	
	Output Voltage	$ I_{OUT}  \le 20 \ \mu A$	4.5V	4.5	4.4	4.4	4.4	V	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$	6.0V	6.0	5.9	5.9	5.9	V	
		$ I_{OUT}  \le 4.0 \text{ mA}$	4.5V	4.2	3.98	3.84	3.7	V	
		$ I_{OUT}  \le 5.2 \text{ mA}$	6.0V	5.7	5.48	5.34	5.2	V	
V <sub>OL</sub>	Maximum LOW Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$	2.0V	0	0.1	0.1	0.1	V	
	Output Voltage	$ I_{OUT}  \le 20 \ \mu A$	4.5V	0	0.1	0.1	0.1	V	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$	6.0V	0	0.1	0.1	0.1	V	
		$ I_{OUT}  \le 4.0 \text{ mA}$	4.5V	0.2	0.26	0.33	0.4	V	
		$ I_{OUT}  \le 5.2 \text{ mA}$	6.0V	0.2	0.26	0.33	0.4	V	
I <sub>IN</sub>	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		±0.1	±1.0	±1.0	μA	
I <sub>CC</sub>	Maximum Quiescent	$V_{IN} = V_{CC}$ or GND	6.0V		2.0	20	40	μA	
	Supply Current	I <sub>OUT</sub> = 0 μA							

Note 4: For a power supply of 5V  $\pm$ 10% the worst case output voltages (V<sub>OH</sub>, and V<sub>OL</sub>) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V<sub>IH</sub> and V<sub>IL</sub> occur at V<sub>CC</sub> = 5.5V and 4.5V respectively. (The V<sub>IH</sub> value at 5.5V is 3.85V.) The worst case leakage current (I<sub>IN</sub>, I<sub>CC</sub>, and I<sub>O2</sub>) occur for CMOS at the higher voltage and so the 6.0V values should be used.

AC Electrical Characteristics						
$V_{\rm CC} = 5$ V, T <sub>A</sub> = <b>Symbol</b>	= $25^{\circ}$ C, C <sub>L</sub> = 15 pF, t <sub>r</sub> = t <sub>f</sub> = 6 ns Parameter	Conditions	Тур	Guaranteed Limit	Units	
<sub>PHL</sub> , t <sub>PLH</sub>	Maximum Propagation Delay		12	20	ns	

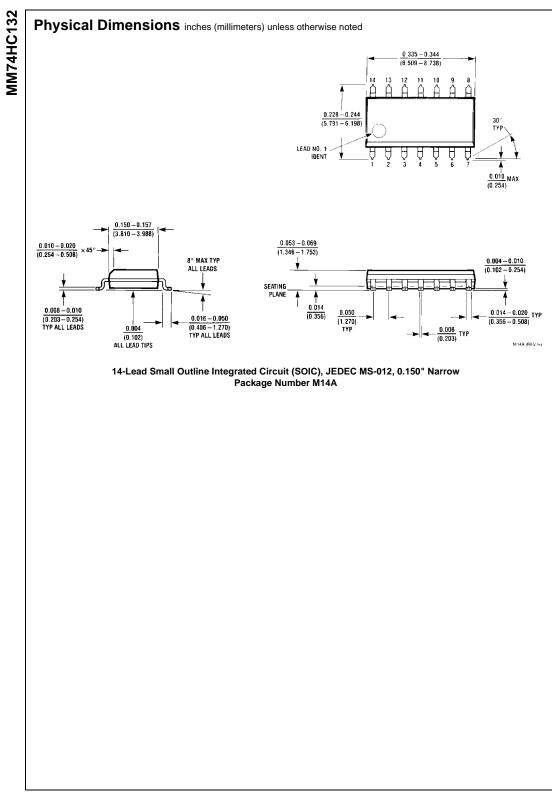
## **AC Electrical Characteristics**

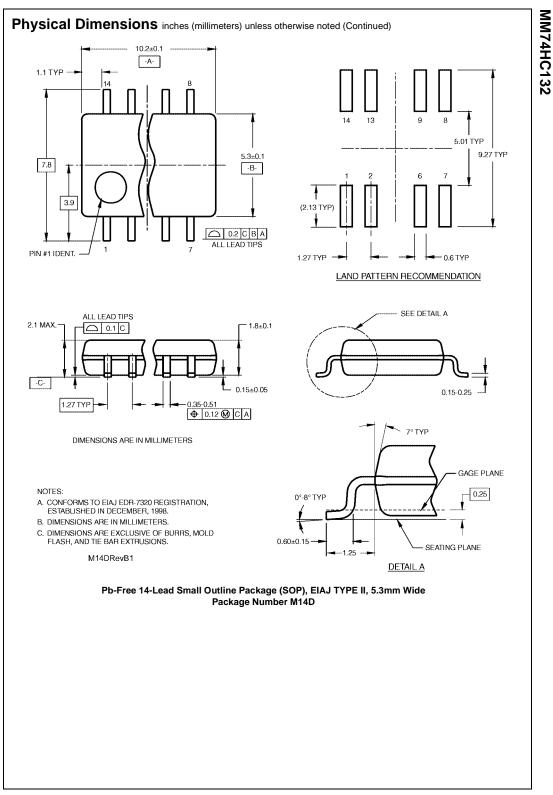
 $V_{CC} = 2.0V$  to 6.0V,  $C_L = 50$  pF,  $t_r = t_f = 6$  ns (unless otherwise specified)

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Symbol	Parameter	Conditions	v <sub>cc</sub>	T <sub>A</sub> = 25°C		T <sub>A</sub> = −40 to 85°C	$T_A = -55$ to $125^{\circ}C$	Units
Oymbol	i alameter			Тур		Guaranteed L	imits	Units
t <sub>PHL</sub> , t <sub>PLH</sub>	Maximum		2.0V	63	125	158	186	ns
	Propagation Delay		4.5V	13	25	32	37	ns
			6.0V	11	21	27	32	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output		2.0V	30	75	95	110	ns
	Rise and Fall Time		4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
C <sub>PD</sub>	Power Dissipation	(per gate)		130				pF
	Capacitance (Note 5)							
CIN	Maximum Input Capacitance				5	10	10	pF

Note 5:  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .

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5

